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a conductive layer formed on a surface of the integrated circuit and operatively coupled to the isolation buried layer at a plurality of points spaced throughout the buried layer, the conductive layer reducing an effective lateral resistance of the isolation buried layer to thereby increase an electrical isolation between the first and second circuit sections.

26. (Amended) A semiconductor device formed on a semiconductor wafer, comprising:
a first circuit section formed in a substrate of the semiconductor wafer;
a second circuit section formed in the substrate, the second circuit section being spaced laterally from the first circuit section;
an isolation buried layer formed under at least a portion of the first circuit section; and
a conductive layer formed on a surface of the semiconductor wafer and electrically coupled to the isolation buried layer at a plurality of points spaced throughout the buried layer, the conductive layer reducing an effective lateral resistance of the isolation buried layer to thereby increase an electrical isolation between the first and second circuit sections.

Please add the following new claims:

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--30. (New) An integrated circuit, comprising:
a first circuit section formed in a substrate;
a second circuit section formed in the substrate, the second circuit section being spaced laterally from the first circuit section;
an isolation buried layer formed under at least a portion of the first circuit section; and
a conductive layer formed on a surface of the integrated circuit and operatively coupled to the isolation buried layer, the conductive layer reducing an effective lateral resistance of the isolation buried layer;
wherein the conductive layer comprises a plurality of conductive traces, the conductive traces intersecting with and connecting to one another to form a net.--

--31. (New) An integrated circuit, comprising:

a first circuit section formed in a substrate;

a second circuit section formed in the substrate, the second circuit section being spaced laterally from the first circuit section;

a first isolation buried layer formed under at least a portion of the first circuit section;

a first conductive layer formed on a surface of the integrated circuit and operatively coupled to the isolation buried layer, the conductive layer reducing an effective lateral resistance of the first isolation buried layer;

a second isolation buried layer formed under at least a portion of the second circuit section; and

a second conductive layer formed on a surface of the integrated circuit and operatively coupled to the second isolation buried layer, the second conductive layer reducing an effective lateral resistance of the second isolation buried layer;

wherein at least one of the first conductive layer and the second conductive layer comprises a plurality of conductive traces, the conductive traces intersecting with and connecting to one another to form a net.--